

<b>PCN Number:</b>	20170906000		<b>PCN Date:</b>	Sept 7, 2017																									
<b>Title:</b>	Qualification of additional Fab site (DMOS6) and Assembly/Bump site (JCAP) option for select devices																												
<b>Customer Contact:</b>	<a href="#">PCN Manager</a>		<b>Dept:</b>	Quality Services																									
<b>Proposed 1<sup>st</sup> Ship Date:</b>	Dec 7, 2017		<b>Estimated Sample Availability:</b>	Date provided at sample request.																									
<b>Change Type:</b>																													
<input checked="" type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Assembly Materials																								
<input type="checkbox"/>	Design	<input type="checkbox"/>	Electrical Specification	<input type="checkbox"/>	Mechanical Specification																								
<input checked="" type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process																								
<input checked="" type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material	<input type="checkbox"/>	Wafer Bump Process																								
<input checked="" type="checkbox"/>	Wafer Fab Site	<input type="checkbox"/>	Wafer Fab Materials	<input type="checkbox"/>	Wafer Fab Process																								
		<input type="checkbox"/>	Part number change																										
<b>PCN Details</b>																													
<b>Description of Change:</b>																													
Texas Instruments is pleased to announce the qualification of an additional fab (DMOS6) and assembly/bump (JCAP) site for the selected devices listed in "Product Affected" section.																													
<table border="1" style="width: 100%; border-collapse: collapse;"> <thead> <tr> <th colspan="4">Current Fab Site</th> <th colspan="4">Additional Fab Site</th> </tr> <tr> <th>Fab Site</th> <th>Process</th> <th>Bump Site</th> <th>Wafer Diameter</th> <th>Fab Site</th> <th>Process</th> <th>Bump Site</th> <th>Wafer Diameter</th> </tr> </thead> <tbody> <tr> <td>RFAB</td> <td>LBC8</td> <td>Clark-BP</td> <td>300 mm</td> <td>DMOS6</td> <td>LBC8</td> <td>JCAP-BP</td> <td>300 mm</td> </tr> </tbody> </table>						Current Fab Site				Additional Fab Site				Fab Site	Process	Bump Site	Wafer Diameter	Fab Site	Process	Bump Site	Wafer Diameter	RFAB	LBC8	Clark-BP	300 mm	DMOS6	LBC8	JCAP-BP	300 mm
Current Fab Site				Additional Fab Site																									
Fab Site	Process	Bump Site	Wafer Diameter	Fab Site	Process	Bump Site	Wafer Diameter																						
RFAB	LBC8	Clark-BP	300 mm	DMOS6	LBC8	JCAP-BP	300 mm																						
There are no material difference between devices currently manufactured and devices built with this manufacturing option.																													
<b>Reason for Change:</b>																													
Continuity of Supply																													
<b>Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):</b>																													
None																													
<b>Anticipated impact on Material Declaration</b>																													
<input checked="" type="checkbox"/>	No Impact to the Material Declaration	<input type="checkbox"/>	Material Declarations or Product Content reports are driven from production data and will be available following the production release. Upon production release the revised reports can be obtained from the <a href="#">TI ECO website</a> .																										
<b>Changes to product identification resulting from this PCN:</b>																													
<b>Fab Site Information:</b>																													
Chip Site		Chip Site Origin Code (20L)	Chip Site Country Code (21L)		Chip Site City																								
RFAB		RFB	USA		Richardson																								
<b>DMOS6</b>		<b>DM6</b>	<b>USA</b>		<b>Dallas</b>																								
<b>Assembly Site Information:</b>																													
Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (21L)		Assembly City																									
Clark	QAB	THA		Bangkok																									
<b>JCAP</b>	<b>JCP</b>	<b>CHN</b>		<b>Jiangyin</b>																									
Sample product shipping label (not actual product label)																													



MADE IN: China  
2DC: 2Q:

MSL 1 / 260C/UNLIM SEAL DT  
04/14/17

OPT:  
ITEM: 73  
LBL: 1A (L)T0:1168



(1P) PTAS2560YFFR  
(Q) 3000 (D) 1710  
(31T) LOT: 7133710JCP  
(4W) SWR (1T) 2855550Z9A  
(P)  
(2P) REV: A0 (V) 0033317  
(20L) CS0: DM6 (21L) CC0: USA  
(22L) AS0: JCP (23L) AC0: CHN

**Topside Device marking (if included):**

Assembly site code for QAB= I

Assembly site code for JCP = W

**Product Affected:**

TAS2560YFFR	TAS2560YFFT
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TI Information  
Selective Disclosure

**Qualification Report**

TAS2560YFF WCSP Device Qual (DMOS6/JCAP)

Approve Date 18-Aug-2017

**Product Attributes**

Attributes	Qual Device: TAS2560YFF	QBS Product Reference: TAS2560YFF	QBS Process Reference: TAS2552YFF	QBS Process Reference: TAS2553YFF	QBS Package Reference: CD3230A0YFF
Wafer Fab Supplier	DMOS6	RFAB	RFAB/DMOS6	RFAB/DMOS6	RFAB
Wafer Process	LBC8LV	LBC8LV	LBC8LV	LBC8LV	LBC7
Assembly Site	JCAP	CLARK-AT	CLARK-AT	CLARK-AT	JCAP
Package Family	DSBGA	DSBGA	DSBGA	DSBGA	DSBGA

-QBS: Qual By Similarity  
-Qual Device TAS2560YFF is qualified at LEVEL1-260C

**Qualification Results**

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: TAS2560YFF	QBS Product Reference: TAS2560YFF	QBS Process Reference: TAS2552YFF	QBS Process Reference: TAS2553YFF	QBS Package Reference: CD3230A0YFF
ED	Electrical Characterization	Per Datasheet Parameters	Pass	Pass	-	Pass	-
ELFR	Early Life Failure Rate, 125C	48 Hours	-	-	-	3/3000/0	-
HAST	Biased HAST, 130C/85%RH	96 Hours	-	-	3/231/0	-	1/77/0
HBM	ESD - HBM	4000 V	1/3/0	1/3/0	-	3/9/0	-
CDM	ESD - CDM	1500 V	1/3/0	1/3/0	-	3/9/0	-
HTOL	Life Test, 125C	1000 Hours	1/77/0	-	-	3/231/0	1/77/0
HTSL	High Temp. Storage Bake, 170C	420 Hours	-	-	3/228/0	-	3/231/0
LU	Latch-up (Per JESD78)	1/6/0	1/6/0	1/6/0	-	3/18/0	-
PD	Physical Dimensions	-	-	-	-	-	3/15/0
SBS	Bump-shear	-	1/50/0	-	3/108/0	-	3/150/0
TC	Temperature Cycle, -55/125C	700 Cycles	1/77/0	-	3/231/0	-	3/231/0
TC	Temperature Cycle, -65/150C	500 Cycles	-	-	-	-	-
UHAST	Unbiased HAST 130C/85%RH	96 Hours	-	-	3/228/0	-	3/231/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable  
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours  
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours  
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles  
Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

Green/Pb-free Status:  
Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

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Asia Pacific	<a href="mailto:PCNAsiaContact@list.ti.com">PCNAsiaContact@list.ti.com</a>
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